

High-Performance RF Transceiver for Narrowband Systems

Check for Samples: [CC1120](#)

1 Introduction

1.1 Features

- **High-Performance, Single-Chip Transceiver**
 - Adjacent Channel Selectivity: 64 dB at 12.5 kHz Offset
 - Blocking Performance: 91 dB at 10 MHz Offset
 - Excellent Receiver Sensitivity:
 - –123 dBm at 1.2 kbps
 - –110 dBm at 50 kbps
 - –127 dBm Using Built-in Coding Gain
 - Very Low Phase Noise: –111 dBc/Hz at 10 kHz offset
- Suitable for Systems Targeting ETSI Category 1 Compliance in 169-MHz and 433-MHz Bands
- High Spectral Efficiency (9.6 kbps in 12.5-kHz Channel in Compliance with FCC Narrowbanding Mandate)
- Separate 128-byte RX and TX FIFOs
- Support for seamless integration with the CC1190 device for increased range giving up to 3-dB improvement in sensitivity and up to +27 dBm output power
- **Power Supply**
 - Wide Supply Voltage Range (2.0 V – 3.6 V)
 - Low Current Consumption:
 - RX: 2 mA in RX Sniff Mode
 - RX: 17 mA Peak Current in Low-Power Mode
 - RX: 22 mA Peak Current in High-Performance Mode
 - TX: 45 mA at +14 dBm
 - Power Down: 0.3 μ A (0.5 μ A with eWOR timer running)
- Programmable Output Power up to +16 dBm with 0.4-dB Step Size
- Automatic Output Power Ramping
- Configurable Data Rates: 0 to 200 kbps
- Supported Modulation Formats: 2-FSK, 2-GFSK, 4-FSK, 4-GFSK, MSK, OOK
- WaveMatch: Advanced Digital Signal Processing for Improved Sync Detect Performance
- RoHS-Compliant 5x5mm QFN 32 Package

1.2 Applications

- Narrowband Ultra-Low-Power Wireless Systems with Channel Spacing Down to 12.5 kHz
- 169-, 315-, 433-, 868-, 915-, 920-, 950-MHz ISM/SRD Band
- Wireless Metering and Wireless Smart Grid (AMR and AMI)
- IEEE 802.15.4g Systems
- Home and Building Automation
- Wireless Alarm and Security Systems
- Industrial Monitoring and Control
- Wireless Healthcare Applications
- Wireless Sensor Networks and Active RFID
- Private Mobile Radio

1.3 Description

The CC1120 device is a fully integrated single-chip radio transceiver designed for high performance at very low-power and low-voltage operation in cost-effective wireless systems. All filters are integrated, thus removing the need for costly external SAW and IF filters. The device is mainly intended for the ISM (Industrial, Scientific, and Medical) and SRD (Short Range Device) frequency bands at 164–192 MHz, 274–320 MHz, 410–480 MHz, and 820–960 MHz.

The CC1120 device provides extensive hardware support for packet handling, data buffering, burst transmissions, clear channel assessment, link quality indication, and Wake-On-Radio. The main operating parameters of the CC1120 device can be controlled through an SPI interface. In a typical system, the CC1120 device will be used together with a microcontroller and only a few external passive components.



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Figure 1-1 shows pin names and locations for the CC1120 device.

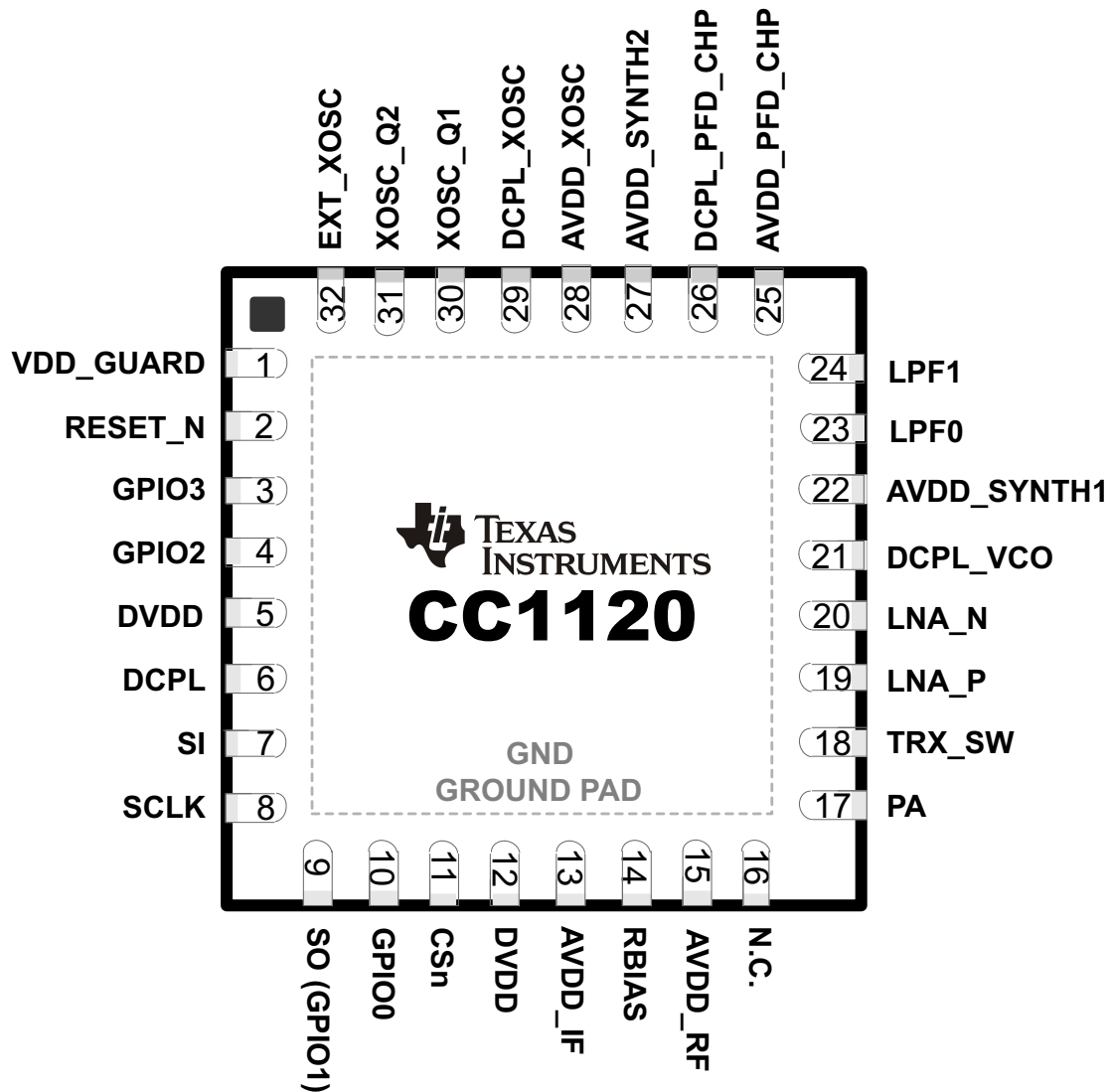


Figure 1-1. Package 5-mm x 5-mm QFN

1.4 Block Diagram

Figure 1-2 shows the system block diagram of the CC1120 devices.

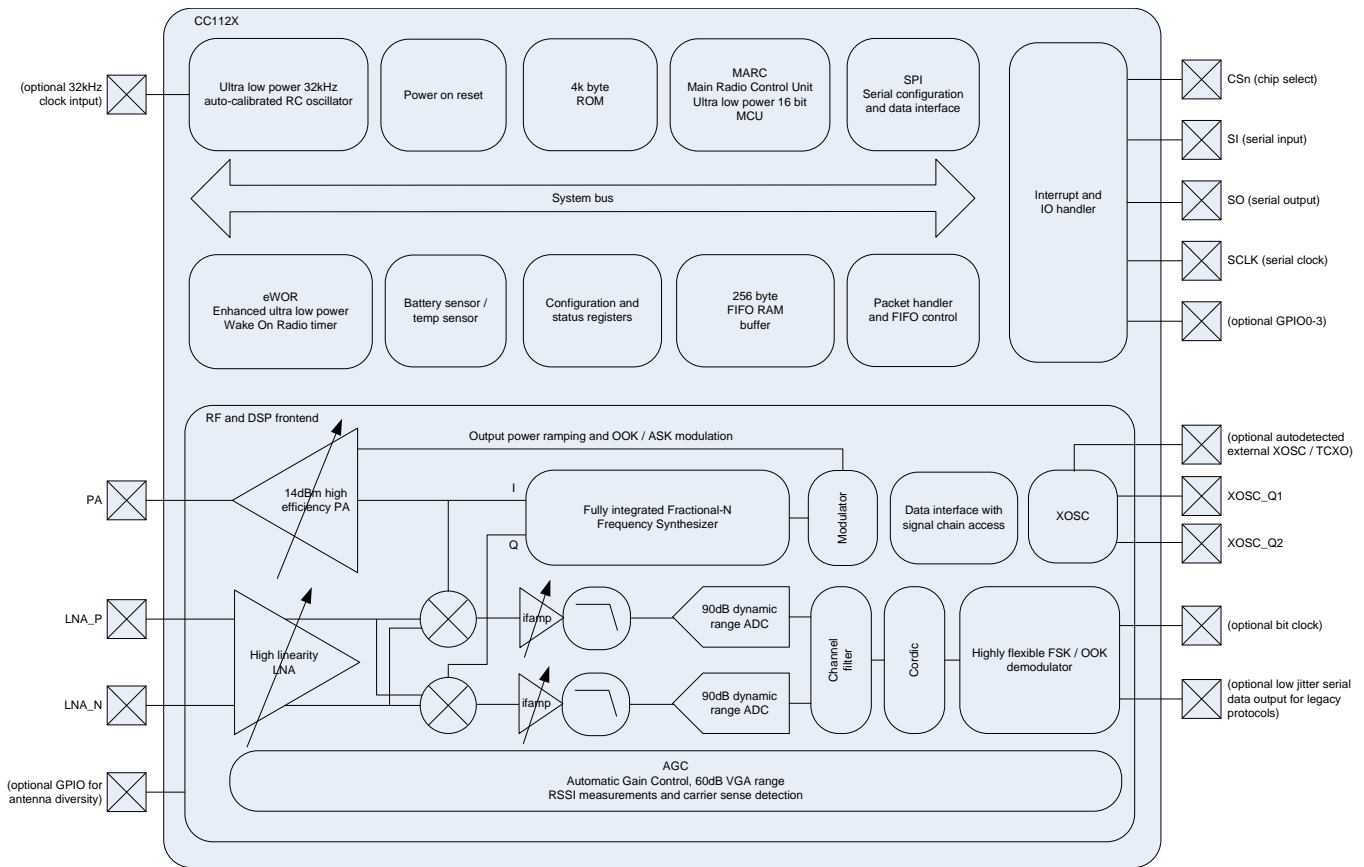


Figure 1-2. System Block Diagram

1.5 Regulations

Suitable for Systems Targeting Compliance with:

- **Europe:** ETSI EN 300 220, ETSI EN 54-25
- **US:** FCC CFR47 Part 15, FCC CFR47 Part 90, 24, and 101
- **Japan:** ARIB RCR STD-T30, ARIB STD-T67, ARIB STD-T108

1.6 Peripherals and Support Functions

- Enhanced Wake-On-Radio (eWOR) functionality for automatic low-power receive polling
- Includes functions for antenna diversity support
- Support for retransmissions
- Support for auto-acknowledge of received packets
- TCXO support and control, also in power modes
- Automatic Clear Channel Assessment (CCA) for Listen-Before-Talk (LBT) systems
- Built-in coding gain support for increased range and robustness
- Digital RSSI measurement
- Temperature sensor

1	Introduction	1	2.13	32-MHz Crystal Oscillator	16
1.1	Features	1	2.14	32-MHz Clock Input (TCXO)	16
1.2	Applications	1	2.15	32-kHz Clock Input	16
1.3	Description	1	2.16	32-kHz RC Oscillator	16
1.4	Block Diagram	3	2.17	I/O and Reset	17
1.5	Regulations	3	2.18	Temperature Sensor	17
1.6	Peripherals and Support Functions	3	2.19	Typical Characteristics	18
	Revision History	5	3	Device Pins	21
2	Device Characteristics	6	3.1	Pin Configuration	21
2.1	Electrical Specifications	6	4	Device Information	23
2.2	Absolute Maximum Ratings	6	4.1	Block Diagram	23
2.3	General Characteristics	6	4.2	Frequency Synthesizer	23
2.4	RF Characteristics	6	4.3	Receiver	24
2.5	Regulatory Standards	7	4.4	Transmitter	24
2.6	Current Consumption, Static Modes	7	4.5	Radio Control and User Interface	24
2.7	Current Consumption, Transmit Modes	8	4.6	Enhanced Wake-On-Radio (eWOR)	24
2.8	Current Consumption, Receive Modes	9	4.7	Sniff Mode	25
2.9	Receive Parameters	9	4.8	Antenna Diversity	25
2.10	Transmit Parameters	14	4.9	WaveMatch	26
2.11	PLL Parameters	15	5	Typical Application Circuit	27
2.12	Wake-up and Timing	16	6	Configuration Software	28

Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

This data sheet revision history highlights the technical changes made to the SWRS112 device-specific data sheet.

Revision	Date	Description / Changes
SWRS112E	Oct. 2013	Changed format to TI data manual Added section on WaveMatch Added links to reference designs Added comment on DC path to VDD / GND required for PA / LNA pins
SWRS112D	March 2013	Added ARIB T-108 to list of regulations Added 1.2 kbps using 10 kHz deviation and 41.7 kHz channel filter Added optimum source / load impedance Added missing unit "dBm" in output power section Added information about the temperature sensor Clarified how the typical performance curves have been measured Corrected wrong deviation for 38.4 kbps sensitivity (was 50 kHz, corrected to 20 kHz) Pin CS_N renamed to CSn to comply with naming convention used in the user guide Updated modulation format information in image rejection sections Stated which ETSI EN 300 220 receiver category that is suitable for low power mode Added deviation and channel filter bandwidth for 300 bps format Added blocking data using settings optimized for best blocking performance at 868/915/920 MHz Clarified under max ratings that I/O voltages should not exceed device supply voltage by more than 0.3 V Various minor spelling errors corrected
SWRS112C	April 2012	Added ground pad on page 1 pin-out and pin description Added TCXO clock input voltage requirement Changed all pin names in pin description and figures to UPPERCASE Changed "PA OUT" to "PA" in block diagram Corrected deviation on 38.4kbps case from 50kHz to 20kHz Corrected error in EM list: CC1120EM_420_970 is corrected to CC1120EM_420_470 Added 274 - 320 MHz band and pointed to app note for more info (added mention of 315 MHz band on front page) Updated sniff mode current to 2 mA Added "WaveMatch:" in front of "Advanced digital signal processing ..." on front page Data rate offset tolerance: specified that 4 byte preamble only applies to 12% offset Removed solder reflow temperature and moisture sensitivity level under absolute max ratings Moved crystal ESR to 'max' column Added History section
SWRS112B	Sept. 2011	Initial release
SWRS112	Aug. 2011	Preliminary Data Sheet

2 Device Characteristics

2.1 Electrical Specifications

All measurements performed on CC1120EM_868_915 rev.1.0.1, CC1120EM_955 rev.1.2.1, CC1120EM_420_470 rev.1.0.1, or CC1120EM_169 rev.1.2

2.2 Absolute Maximum Ratings

Parameter	Min	Typ	Max	Unit	Condition
Supply voltage (VDD) (all supply pins must have the same voltage)	–0.3		3.9	V	
Storage temperature range	–40		125	°C	
ESD			2000	V	HBM
ESD			500	V	CDM
Input RF level			+10	dBm	
Voltage on any digital pin	–0.3		VDD+0.3 max 3.9	V	
Voltage on analog pins (including DCPL pins)	–0.3		2.0	V	

2.3 General Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Voltage supply range	2.0		3.6	V	
Temperature range	–40		85	°C	

2.4 RF Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Frequency bands	820		960	MHz	
	410		480	MHz	
	274		320	MHz	Please see application note AN115, <i>Using the CC112x/CC1175 at 274 to 320 MHz</i> , for more information
	164		192	MHz	
Frequency resolution		30		Hz	In 820–950 MHz band
		15		Hz	In 410–480 MHz band
		6		Hz	In 164–192 MHz band
Data rate	0		200	kbps	Packet mode
	0		100	kbps	Transparent mode
Data rate step size		1e-4		bps	

2.5 Regulatory Standards

Performance Mode	Frequency Band	Suitable for compliance with	Comments
High-performance mode	820–960 MHz	ARIB T-96 ARIB T-108 ETSI EN 300 220 category 2 ETSI EN 54-25 FCC PART 101 FCC PART 24 SUBMASK D FCC PART 15.247 FCC PART 15.249 FCC PART 90 MASK G FCC PART 90 MASK J	Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender such as the CC1190 device
	410–480 MHz	ARIB T-67 ARIB RCR STD-30 ETSI EN 300 220 category 1 FCC PART 90 MASK D FCC PART 90 MASK G	Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender
	164–192 MHz	ETSI EN 300 220 category 1 FCC PART 90 MASK D	Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender
Low-power mode	820–960 MHz	ETSI EN 300 220 category 2 FCC PART 15.247 FCC PART 15.249	
	410–480 MHz	ETSI EN 300 220 category 2	
	164–192 MHz	ETSI EN 300 220 category 2	

2.6 Current Consumption, Static Modes

 $T_A = 25^{\circ}\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Power down with retention		0.3	1	μA	
		0.5		μA	Low-power RC oscillator running
XOFF mode		170		μA	Crystal oscillator / TCXO disabled
IDLE mode		1.3		mA	Clock running, system waiting with no radio activity

2.7 Current Consumption, Transmit Modes

2.7.1 950-MHz Band (High-Performance Mode)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
TX current consumption +10 dBm		37		mA	
TX current consumption 0 dBm		26		mA	

2.7.2 868-, 915-, and 920-MHz Bands (High-Performance Mode)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
TX current consumption +14 dBm		45		mA	
TX current consumption +10 dBm		34		mA	

2.7.3 434-MHz Band (High-Performance Mode)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
TX current consumption +15 dBm		50		mA	
TX current consumption +14 dBm		45		mA	
TX current consumption +10 dBm		34		mA	

2.7.4 169-MHz Band (High-Performance Mode)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
TX current consumption +15 dBm		54		mA	
TX current consumption +14 dBm		49		mA	
TX current consumption +10 dBm		41		mA	

2.7.5 Low-Power Mode

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
TX current consumption +10 dBm		32		mA	

2.8 Current Consumption, Receive Modes

2.8.1 High-Performance Mode

 $T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
RX Wait for sync 1.2 kbps, 4-byte preamble 38.4 kbps, 4-byte preamble		2 13.4		mA mA	Using RX sniff mode, where the receiver wakes up at regular intervals to look for an incoming packet
RX Peak Current 433-, 868-, 915-, 920-, and 950-MHz bands 169-MHz band		22 23		mA mA	Peak current consumption during packet reception at the sensitivity threshold
Average current consumption Check for data packet every 1 second using Wake on Radio		15		μA	50 kbps, 5-byte preamble, 40-kHz RC oscillator used as sleep timer

2.8.2 Low-Power Mode

 $T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
RX Peak Current Low-power RX mode 1.2 kbps		17		mA	Peak current consumption during packet reception at the sensitivity level

2.9 Receive Parameters

All RX measurements made at the antenna connector, to a bit error rate (BER) limit of 1%.

2.9.1 General Receive Parameters (High-Performance Mode)

 $T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Saturation		+10		dBm	
Digital Channel Filter Programmable Bandwidth	8		200	kHz	
IIP3, Normal mode		–14		dBm	At maximum gain
IIP3, High Linearity mode		–8		dBm	Using 6 dB gain reduction in front end
Datarate Offset Tolerance		± 12		%	With carrier sense detection enabled and assuming 4 byte preamble
		± 0.2		%	With carrier sense detection disabled
Spurious Emissions 1–13 GHz (VCO leakage at 3.5 GHz) 30 MHz to 1 GHz		–56 < –57		dBm dBm	Radiated emissions measured according to ETSI EN 300 220, $f_c = 869.5\text{ MHz}$
Optimum Source Impedance 868-, 915-, and 920-MHz bands 433-MHz band 169-MHz band		60 + j60 / 30+j30 100 + j60 / 50+ j30 140 + j40 / 70 + j20		Ω Ω Ω	(Differential or Single-Ended RX Configurations)

2.9.2 RX Performance in 950-MHz Band (High-Performance Mode)

T_A = 25°C, VDD = 3.0 V if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Sensitivity Note: Sensitivity can be improved if the TX and RX matching networks are separated.		–120		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
		–114		dBm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
		–107		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz ⁽¹⁾
		–100		dBm	200 kbps, DEV=83 kHz (outer symbols), CHF=200 kHz ⁽¹⁾ , 4GFSK ⁽²⁾
Blocking and Selectivity 1.2 kbps 2FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		51		dB	± 12.5 kHz (adjacent channel)
		52		dB	± 25 kHz (alternate channel)
		73		dB	± 1 MHz
		76		dB	± 2 MHz
		81		dB	± 10 MHz
Blocking and Selectivity 1.2 kbps 2FSK, 50-kHz channel separation, 20-kHz deviation, 50-kHz channel filter		47		dB	± 50 kHz (adjacent channel)
		48		dB	+ 100 kHz (alternate channel)
		69		dB	± 1 MHz
		71		dB	± 2 MHz
		78		dB	± 10 MHz
Blocking and Selectivity 50 kbps 2GFSK, 200-kHz channel separation, 25-kHz deviation, 100-kHz channel filter (Same modulation format as 802.15.4g Mandatory Mode)		43		dB	± 200 kHz (adjacent channel)
		51		dB	± 400 kHz (alternate channel)
		62		dB	± 1 MHz
		65		dB	± 2 MHz
		71		dB	± 10 MHz
Blocking and Selectivity 200 kbps 4GFSK, 83-kHz deviation (outer symbols), 200-kHz channel filter, zero IF		37		dB	± 200 kHz (adjacent channel)
		44		dB	± 400 kHz (alternate channel)
		55		dB	± 1 MHz
		58		dB	± 2 MHz
		64		dB	± 10 MHz

(1) DEV is short for deviation, CHF is short for Channel Filter Bandwidth

(2) BT=0.5 is used in all GFSK measurements

2.9.3 RX Performance in 868-, 915-, and 920-MHz Bands (High-Performance Mode)

 $T_A = 25^{\circ}\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Sensitivity		-127		dBm	300 bps with coding gain (using a PN spreading sequence with 4 chips per databit) DEV=4 kHz CHF=10 kHz ⁽¹⁾
		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
		-120		dBm	1.2 kbps, DEV=10 kHz CHF=42 kHz ⁽¹⁾
		-117		dBm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
		-114		dBm	4.8 kbps OOK
		-110		dBm	38.4 kbps, DEV=20 kHz CHF=100 kHz ⁽¹⁾
		-110		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz ⁽¹⁾
		-103		dBm	200 kbps, DEV=83 kHz (outer symbols), CHF=200 kHz ⁽¹⁾ , 4GFSK
Blocking and Selectivity 1.2-kbps 2-FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		54		dB	± 12.5 kHz (adjacent channel)
		54		dB	± 25 kHz (alternate channel)
		75		dB	± 1 MHz
		79		dB	± 2 MHz
		87		dB	± 10 MHz
Blocking 1.2-kbps 2-FSK, 12.5-kHz channel separation, using settings optimized for blocking performance (3-kHz deviation, 7.8-kHz channel filter, minimum loop bandwidth)		78		dB	± 1 kHz
		82		dB	± 2 kHz
		88		dB	± 8 MHz
		88		dB	± 10 MHz
Blocking and Selectivity 1.2-kbps 2-FSK, 50-kHz channel separation, 20-kHz deviation, 50-kHz channel filter		48		dB	± 50 kHz (adjacent channel)
		48		dB	+ 100 kHz (alternate channel)
		69		dB	± 1 MHz
		74		dB	± 2 MHz
		81		dB	± 10 MHz
Blocking and Selectivity 38.4-kbps 2-GFSK, 100-kHz channel separation, 20-kHz deviation, 100-kHz channel filter		42		dB	+ 100 kHz (adjacent channel)
		43		dB	± 200 kHz (alternate channel)
		62		dB	± 1 MHz
		66		dB	± 2 MHz
		74		dB	± 10 MHz
Blocking and Selectivity 50-kbps 2-GFSK, 200-kHz channel separation, 25-kHz deviation, 100-kHz channel filter (Same modulation format as 802.15.4g Mandatory Mode)		43		dB	± 200 kHz (adjacent channel)
		50		dB	± 400 kHz (alternate channel)
		61		dB	± 1 MHz
		65		dB	± 2 MHz
		74		dB	± 10 MHz
Blocking and Selectivity 200-kbps 4-GFSK, 83-kHz deviation (outer symbols), 200-kHz channel filter, zero IF		36		dB	± 200 kHz (adjacent channel)
		44		dB	± 400 kHz (alternate channel)
		55		dB	± 1 MHz
		59		dB	± 2 MHz
		67		dB	± 10 MHz
Image Rejection (Image compensation enabled)		54		dB	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾ , image at -125 kHz

(1) DEV is short for deviation, CHF is short for Channel Filter Bandwidth

2.9.4 RX Performance in 434-MHz Band (High-Performance Mode)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Sensitivity		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
		-109		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz
		-116		dBm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
Blocking and Selectivity 1.2 kbps 2FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		60		dB	$\pm 12.5\text{ kHz}$ (adjacent channel)
		60		dB	$\pm 25\text{ kHz}$ (alternate channel)
		79		dB	$\pm 1\text{ MHz}$
		82		dB	$\pm 2\text{ MHz}$
		91		dB	$\pm 10\text{ MHz}$
Blocking and Selectivity 1.2 kbps 2FSK, 50-kHz channel separation, 20-kHz deviation, 50-kHz channel filter		54		dB	$\pm 50\text{ kHz}$ (adjacent channel)
		54		dB	$+ 100\text{ kHz}$ (alternate channel)
		74		dB	$\pm 1\text{ MHz}$
		78		dB	$\pm 2\text{ MHz}$
		86		dB	$\pm 10\text{ MHz}$
Blocking and Selectivity 38.4 kbps 2GFSK, 100-kHz channel separation, 20-kHz deviation, 100-kHz channel filter		47		dB	$+ 100\text{ kHz}$ (adjacent channel)
		50		dB	$\pm 200\text{ kHz}$ (alternate channel)
		67		dB	$\pm 1\text{ MHz}$
		71		dB	$\pm 2\text{ MHz}$
		78		dB	$\pm 10\text{ MHz}$

(1) DEV is short for deviation, CHF is short for Channel Filter Bandwidth

2.9.5 RX Performance in 169-MHz Band (High-Performance Mode)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Sensitivity		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
		-117		dbm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
Blocking and Selectivity 1.2 kbps 2FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		64		dB	$\pm 12.5\text{ kHz}$ (adjacent channel)
		66		dB	$\pm 25\text{ kHz}$ (alternate channel)
		82		dB	$\pm 1\text{ MHz}$
		83		dB	$\pm 2\text{ MHz}$
		89		dB	$\pm 10\text{ MHz}$
Blocking and Selectivity 1.2 kbps 2FSK, 50-kHz channel separation, 20-kHz deviation, 50-kHz channel filter		60		dB	$\pm 50\text{ kHz}$ (adjacent channel)
		60		dB	$+ 100\text{ kHz}$ (alternate channel)
		76		dB	$\pm 1\text{ MHz}$
		77		dB	$\pm 2\text{ MHz}$
		83		dB	$\pm 10\text{ MHz}$
Spurious Response Rejection 1.2 kbps 2FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		70		dB	
Image Rejection (Image compensation enabled)		66		dB	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾ , image at -125 kHz

(1) DEV is short for deviation, CHF is short for Channel Filter Bandwidth

2.9.6 RX Performance in Low-Power Mode

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Sensitivity		–111		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
		–99		dBm	38.4 kbps, DEV=50 kHz CHF=100 kHz ⁽¹⁾
		–99		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz ⁽¹⁾
Blocking and Selectivity 1.2 kbps 2FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		46		dB	± 12.5 kHz (adjacent channel)
		46		dB	± 25 kHz (alternate channel)
		73		dB	± 1 MHz
		78		dB	± 2 MHz
		79		dB	± 10 MHz
Blocking and Selectivity 1.2 kbps 2FSK, 50-kHz channel separation, 20-kHz deviation, 50-kHz channel filter		43		dB	± 50 kHz (adjacent channel)
		45		dB	+ 100 kHz (alternate channel)
		71		dB	± 1 MHz
		74		dB	± 2 MHz
		75		dB	± 10 MHz
Blocking and Selectivity 38.4 kbps 2GFSK, 100-kHz channel separation, 20-kHz deviation, 100-kHz channel filter		37		dB	+ 100 kHz (adjacent channel)
		43		dB	+ 200 kHz (alternate channel)
		58		dB	± 1 MHz
		62		dB	± 2 MHz
		64		dB	+ 10 MHz
Blocking and Selectivity 50 kbps 2GFSK, 200-kHz channel separation, 25-kHz deviation, 100-kHz channel filter (Same modulation format as 802.15.4g Mandatory Mode)		43		dB	+ 200 kHz (adjacent channel)
		52		dB	+ 400 kHz (alternate channel)
		60		dB	± 1 MHz
		64		dB	± 2 MHz
		65		dB	± 10 MHz
Saturation		+10		dBm	

(1) DEV is short for deviation, CHF is short for Channel Filter Bandwidth

2.10 Transmit Parameters

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Max output power		+12		dBm	At 950 MHz
		+14		dBm	At 915- and 920-MHz
		+15		dBm	At 915- and 920-MHz with $V_{DD} = 3.6\text{ V}$
		+15		dBm	At 868 MHz
		+16		dBm	At 868 MHz with $V_{DD} = 3.6\text{ V}$
		+15		dBm	At 433 MHz
Min output power		+16		dBm	At 433 MHz with $V_{DD} = 3.6\text{ V}$
		+15		dBm	At 169 MHz
Output power step size		+16		dBm	At 169 MHz with $V_{DD} = 3.6\text{ V}$
		–11		dBm	Within fine step size range
Adjacent channel power		–40		dBm	Within coarse step size range
		0.4		dB	Within fine step size range
		–75		dBc	4-GFSK 9.6 kbps in 12.5-kHz channel, measured in 100-Hz bandwidth at 434 MHz (FCC Part 90 Mask D compliant)
Spurious emissions (not including harmonics)		–58		dBc	4-GFSK 9.6 kbps in 12.5-kHz channel, measured in 8.75-kHz bandwidth (ETSI EN 300 220 compliant)
		–61		dBc	2-GFSK 2.4 kbps in 12.5-kHz channel, 1.2-kHz deviation
Harmonics		< –60		dBm	
2nd Harm, 169 MHz		–39		dBm	Transmission at +14 dBm (or maximum allowed in applicable band where this is less than +14 dBm) using TI reference design. Emissions measured according to ARIB T-96 in 950-MHz band, ETSI EN 300-220 in 170-, 433-, and 868-MHz bands and FCC part 15.247 in 450- and 915-MHz band. Fourth harmonic in 915-MHz band will require extra filtering to meet FCC requirements if transmitting for long intervals (>50-ms periods).
3rd Harm, 169 MHz		–58		dBm	
2nd Harm, 433 MHz		–56		dBm	
3rd Harm, 433 MHz		–51		dBm	
2nd Harm, 450 MHz		–60		dBm	
3rd Harm, 450 MHz		–45		dBm	
2nd Harm, 868 MHz		–40		dBm	
3rd Harm, 868 MHz		–42		dBm	
2nd Harm, 915 MHz		56		dBuV/m	
3rd Harm, 915 MHz		52		dBuV/m	
4th Harm, 915 MHz		60		dBuV/m	
2nd Harm, 950 MHz		–58		dBm	
3rd Harm, 950 MHz		–42		dBm	
Optimum load					
Impedance 868-, 915-, and 920-MHz bands		$35 + j35$		Ω	
433 MHz band		$55 + j25$		Ω	
169 MHz band		$80 + j0$		Ω	

2.11 PLL Parameters

2.11.1 High-Performance Mode

 $T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Phase noise in 950-MHz band		–99		dBc/Hz	$\pm 10\text{ kHz offset}$
		–99		dBc/Hz	$\pm 100\text{ kHz offset}$
		–123		dBc/Hz	$\pm 1\text{ MHz offset}$
Phase noise in 868-, 915-, 920-MHz bands		–99		dBc/Hz	$\pm 10\text{ kHz offset}$
		–100		dBc/Hz	$\pm 100\text{ kHz offset}$
		–122		dBc/Hz	$\pm 1\text{ MHz offset}$
Phase noise in 433-MHz band		–106		dBc/Hz	$\pm 10\text{ kHz offset}$
		–107		dBc/Hz	$\pm 100\text{ kHz offset}$
		–127		dBc/Hz	$\pm 1\text{ MHz offset}$
Phase noise in 169-MHz band		–111		dBc/Hz	$\pm 10\text{ kHz offset}$
		–116		dBc/Hz	$\pm 100\text{ kHz offset}$
		–135		dBc/Hz	$\pm 1\text{ MHz offset}$

2.11.2 Low-Power Mode

 $T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Phase noise in 950-MHz band		–90		dBc/Hz	$\pm 10\text{ kHz offset}$
		–92		dBc/Hz	$\pm 100\text{ kHz offset}$
		–124		dBc/Hz	$\pm 1\text{ MHz offset}$
Phase noise in 868-, 915-, 920-MHz bands		–95		dBc/Hz	$\pm 10\text{ kHz offset}$
		–95		dBc/Hz	$\pm 100\text{ kHz offset}$
		–124		dBc/Hz	$\pm 1\text{ MHz offset}$
Phase noise in 433-MHz band		–98		dBc/Hz	$\pm 10\text{ kHz offset}$
		–102		dBc/Hz	$\pm 100\text{ kHz offset}$
		–129		dBc/Hz	$\pm 1\text{ MHz offset}$
Phase noise in 169-MHz band		–106		dBc/Hz	$\pm 10\text{ kHz offset}$
		–110		dBc/Hz	$\pm 100\text{ kHz offset}$
		–136		dBc/Hz	$\pm 1\text{ MHz offset}$

2.12 Wake-up and Timing

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Powerdown to IDLE		0.4		ms	Depends on crystal
IDLE to RX/TX		166		μs	Calibration disabled
		461		μs	Calibration enabled
RX/TX turnaround		50		μs	
RX/TX to IDLE time		296		μs	Calibrate when leaving RX/TX enabled
		0		μs	Calibrate when leaving RX/TX disabled
Frequency synthesizer calibration		391		μs	When using SCAL strobe
Minimum required number of preamble bytes		0.5		bytes	Required for RF front end gain settling only. Digital demodulation does not require preamble for settling
Time from start RX until valid RSSI Including gain settling (function of channel bandwidth. Programmable for trade-off between speed and accuracy)		4.6		ms	12.5-kHz channels
		0.3		ms	200-kHz channels

2.13 32-MHz Crystal Oscillator

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Crystal frequency	32		33.6	MHz	Note: It is recommended that the crystal frequency is chosen so that the RF channel(s) are >1 MHz away from multiples of XOSC in TX and XOSC/2 in RX.
Load capacitance (C_L)		10		pF	
ESR			60	Ω	Simulated over operating conditions
Start-up time		0.4		ms	Depends on crystal

2.14 32-MHz Clock Input (TCXO)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Clock frequency	32		33.6	MHz	
Clock input amplitude (peak-to-peak)	0.8		VDD	V	Simulated over operating conditions

2.15 32-kHz Clock Input

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Clock frequency		32		kHz	
32 kHz clock input pin input high voltage	0.8xVDD			V	
32 kHz clock input pin input high voltage			0.2xVDD	V	

2.16 32-kHz RC Oscillator

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Frequency		32		kHz	After calibration
Frequency accuracy after calibration		± 0.1		%	Relative to frequency reference (32-MHz crystal or TCXO)
Initial calibration time		1.6		ms	

2.17 I/O and Reset

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Logic input high voltage	0.8xVDD			V	
Logic input low voltage			0.2xVDD	V	
Logic output high voltage	0.8xVDD			V	At 4-mA output load or less
Logic output low voltage			0.2xVDD	V	
Power-on reset threshold		1.3		V	Voltage on DVDD pin

2.18 Temperature Sensor

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$ if nothing else stated

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensor range	–40		85	$^\circ\text{C}$	
Temperature coefficient		2.66		mV / $^\circ\text{C}$	Change in sensor output voltage versus change in temperature
Typical output voltage		794		mV	Typical sensor output voltage at $T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$
VDD coefficient		1.17		mV / V	Change in sensor output voltage versus change in VDD

The CC1120 device can be configured to provide a voltage proportional to temperature on GPIO1. The temperature can be estimated by measuring this voltage (See [Section 2.18, Temperature Sensor](#)). For more information, see the CC1120 user guide ([SWRU295](#)).

2.19 Typical Characteristics

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{ V}$, $f_c = 869.5\text{ MHz}$ if nothing else stated

All measurements performed on CC1120EM_868_915 rev.1.0.1, CC1120EM_955 rev.1.2.1, CC1120EM_420_470 rev.1.0.1, or CC1120EM_169 rev.1.2

Figure 2-12 was measured at the 50- Ω antenna connector.

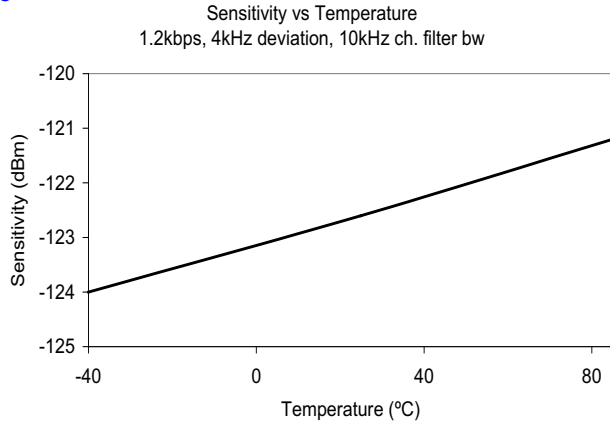


Figure 2-1.

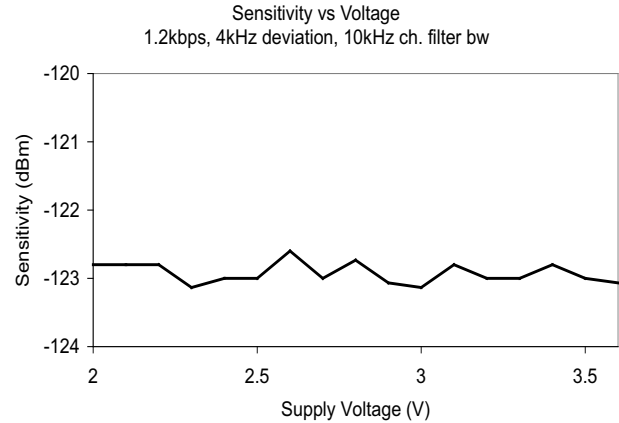


Figure 2-2.

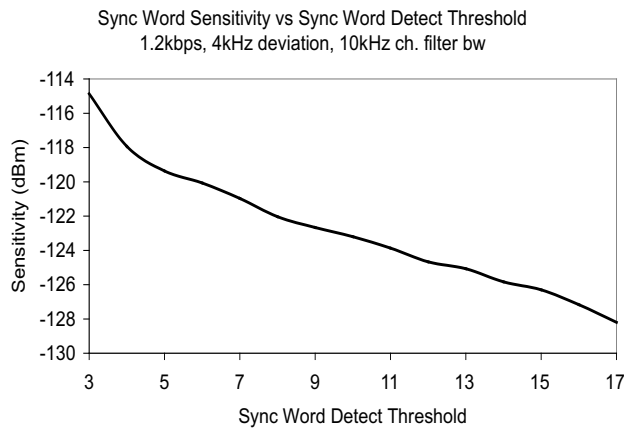


Figure 2-3.

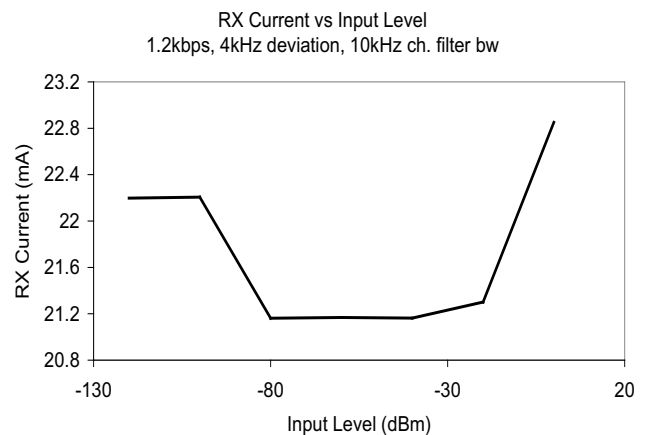


Figure 2-4.

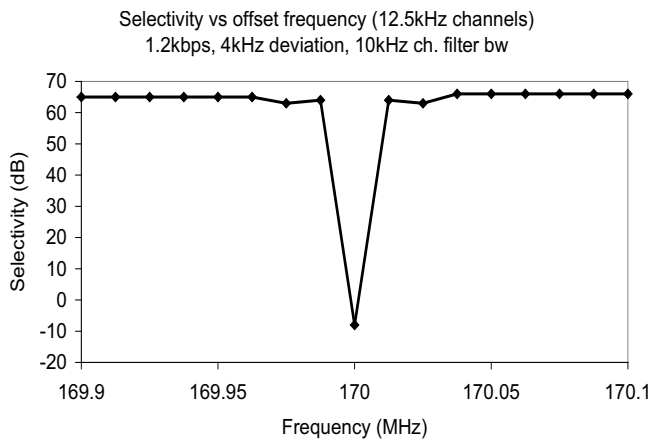


Figure 2-5.

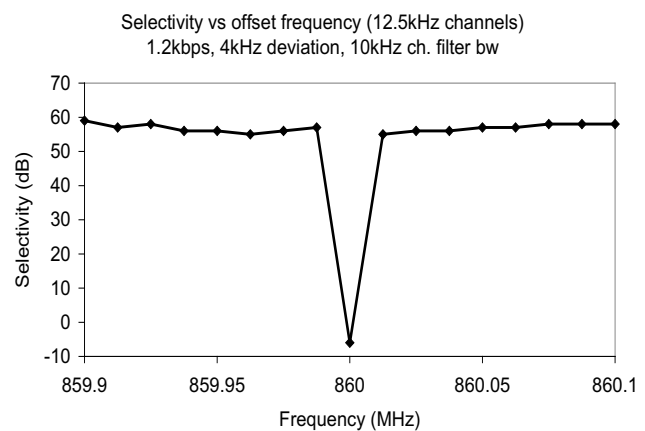


Figure 2-6.

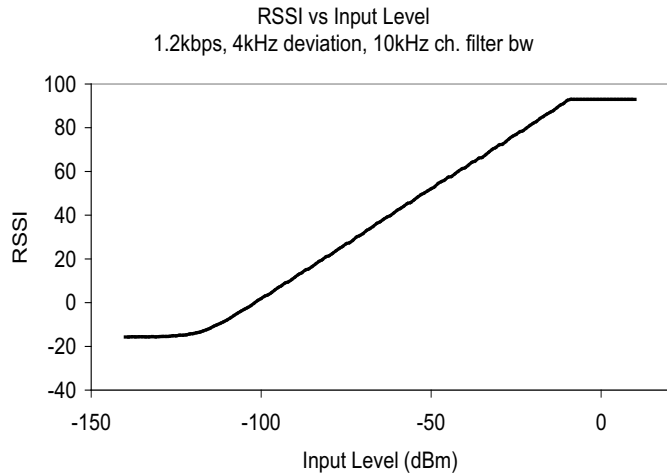


Figure 2-7.

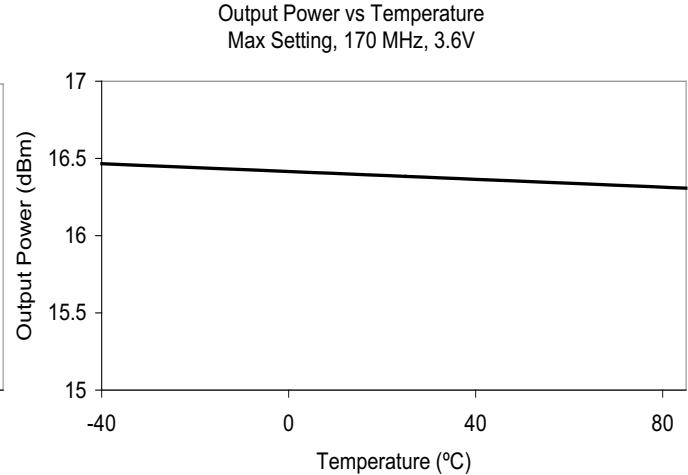


Figure 2-8.

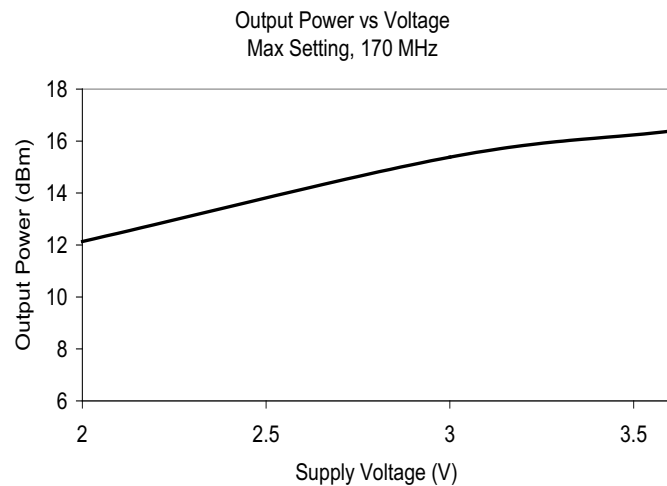


Figure 2-9.

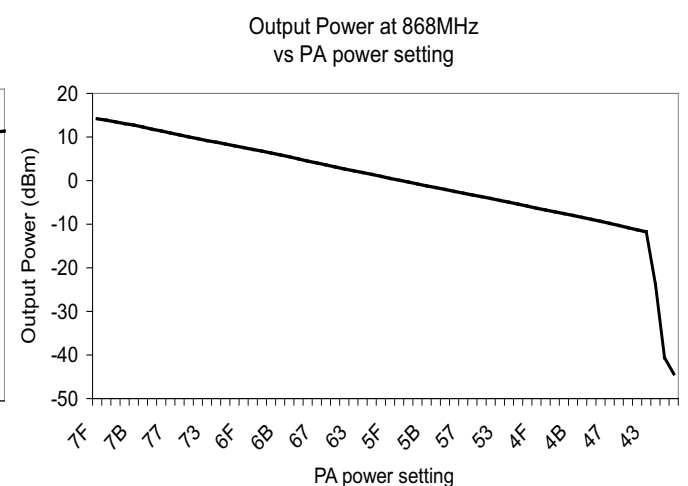


Figure 2-10.

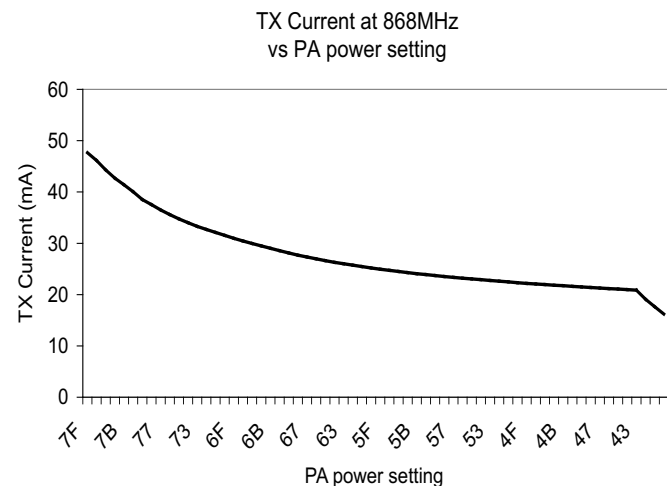


Figure 2-11.

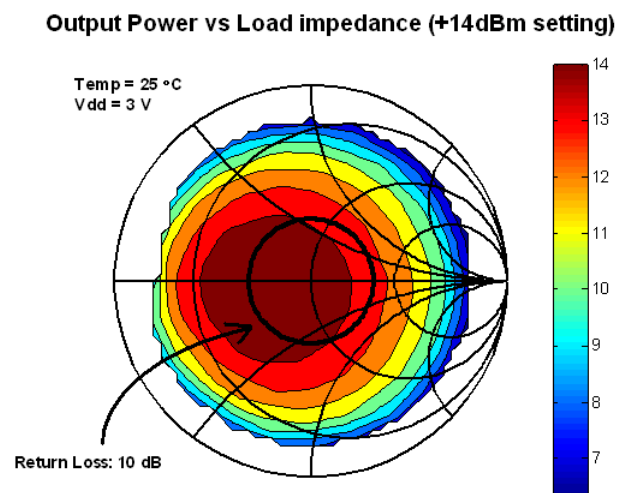


Figure 2-12.

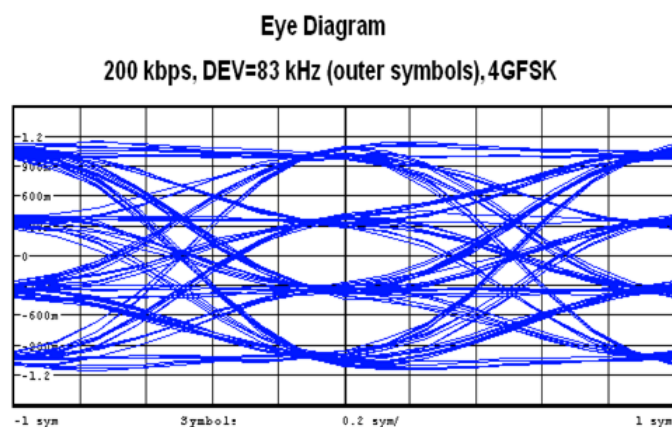


Figure 2-13.

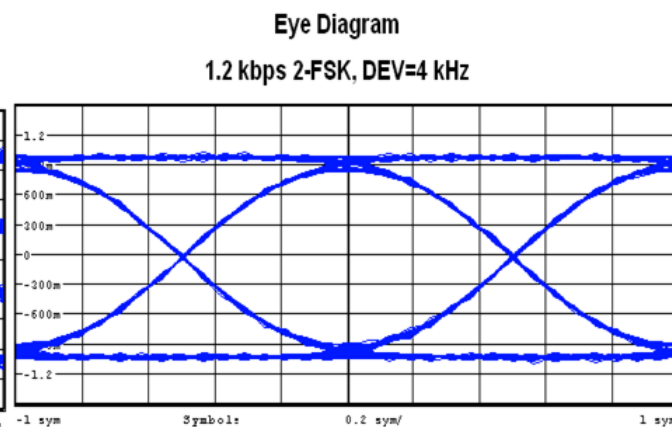


Figure 2-14.

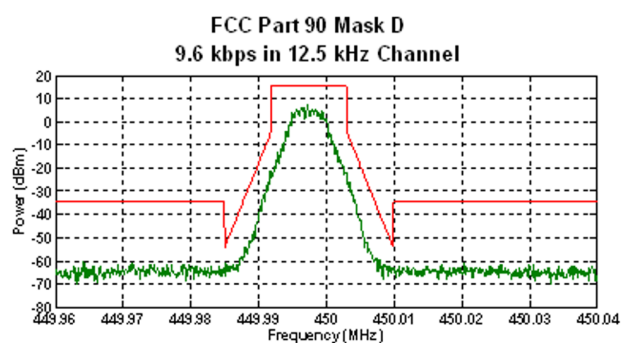


Figure 2-15.

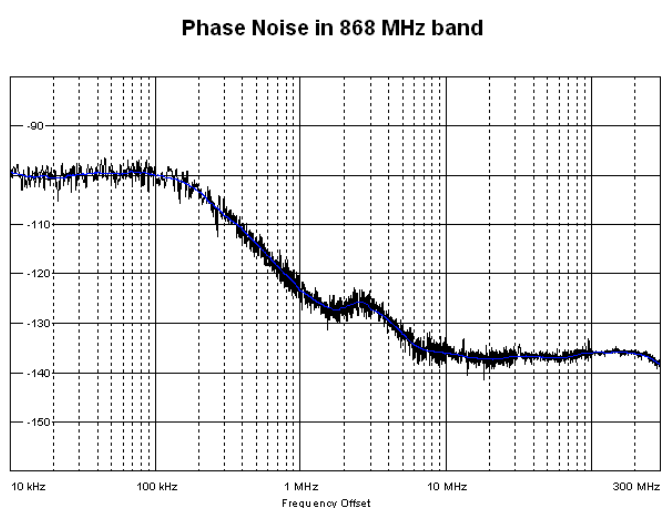


Figure 2-16.

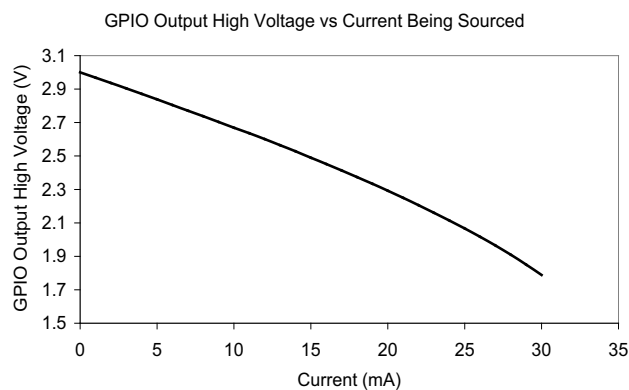


Figure 2-17.

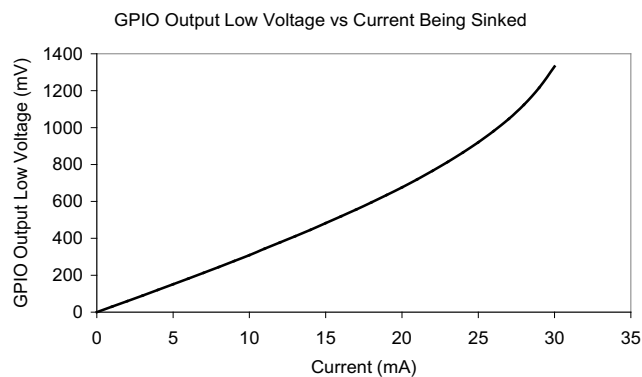


Figure 2-18.

3 Device Pins

3.1 Pin Configuration

The following table lists the pin-out configuration for the CC1120 device.

Pin No.	Pin Name	Type / Direction	Description
1	VDD_GUARD	Power	2.0–3.6 V VDD
2	RESET_N	Digital input	Asynchronous, active-low digital reset
3	GPIO3	Digital I/O	General-purpose I/O
4	GPIO2	Digital I/O	General-purpose I/O
5	DVDD	Power	2.0–3.6 VDD to internal digital regulator
6	DCPL	Power	Digital regulator output to external decoupling capacitor
7	SI	Digital input	Serial data in
8	SCLK	Digital input	Serial data clock
9	SO(GPIO1)	Digital I/O	Serial data out (general-purpose I/O)
10	GPIO0	Digital I/O	General-purpose I/O
11	CSn	Digital input	Active-low chip select
12	DVDD	Power	2.0–3.6 V VDD
13	AVDD_IF	Power	2.0–3.6 V VDD
14	RBIAS	Analog	External high-precision resistor
15	AVDD_RF	Power	2.0–3.6 V VDD
16	N.C.		Not connected
17	PA	Analog	Single-ended TX output (requires DC path to VDD)
18	TRX_SW	Analog	TX and RX switch. Connected internally to GND in TX and floating (high-impedance) in RX.
19	LNA_P	Analog	Differential RX input (requires DC path to ground)
20	LNA_N	Analog	Differential RX input (requires DC path to ground)
21	DCPL_VCO	Power	Pin for external decoupling of VCO supply regulator
22	AVDD_SYNTH1	Power	2.0–3.6 V VDD
23	LPF0	Analog	External loop filter components
24	LPF1	Analog	External loop filter components
25	AVDD_PFD_CHP	Power	2.0–3.6 V VDD
26	DCPL_PFD_CHP	Power	Pin for external decoupling of PFD and CHP regulator
27	AVDD_SYNTH2	Power	2.0–3.6 V VDD
28	AVDD_XOSC	Power	2.0–3.6 V VDD
29	DCPL_XOSC	Power	Pin for external decoupling of XOSC supply regulator
30	XOSC_Q1	Analog	Crystal oscillator pin 1 (must be grounded if a TCXO or other external clock connected to EXT_XOSC is used)
31	XOSC_Q2	Analog	Crystal oscillator pin 2 (must be left floating if a TCXO or other external clock connected to EXT_XOSC is used)
32	EXT_XOSC	Digital input	Pin for external clock input (must be grounded if a regular crystal connected to XOSC_Q1 and XOSC_Q2 is used)
–	GND	Ground pad	The ground pad must be connected to a solid ground plane.

4 Device Information

4.1 Block Diagram

Figure 4-1 shows the system block diagram of the CC1120 devices.

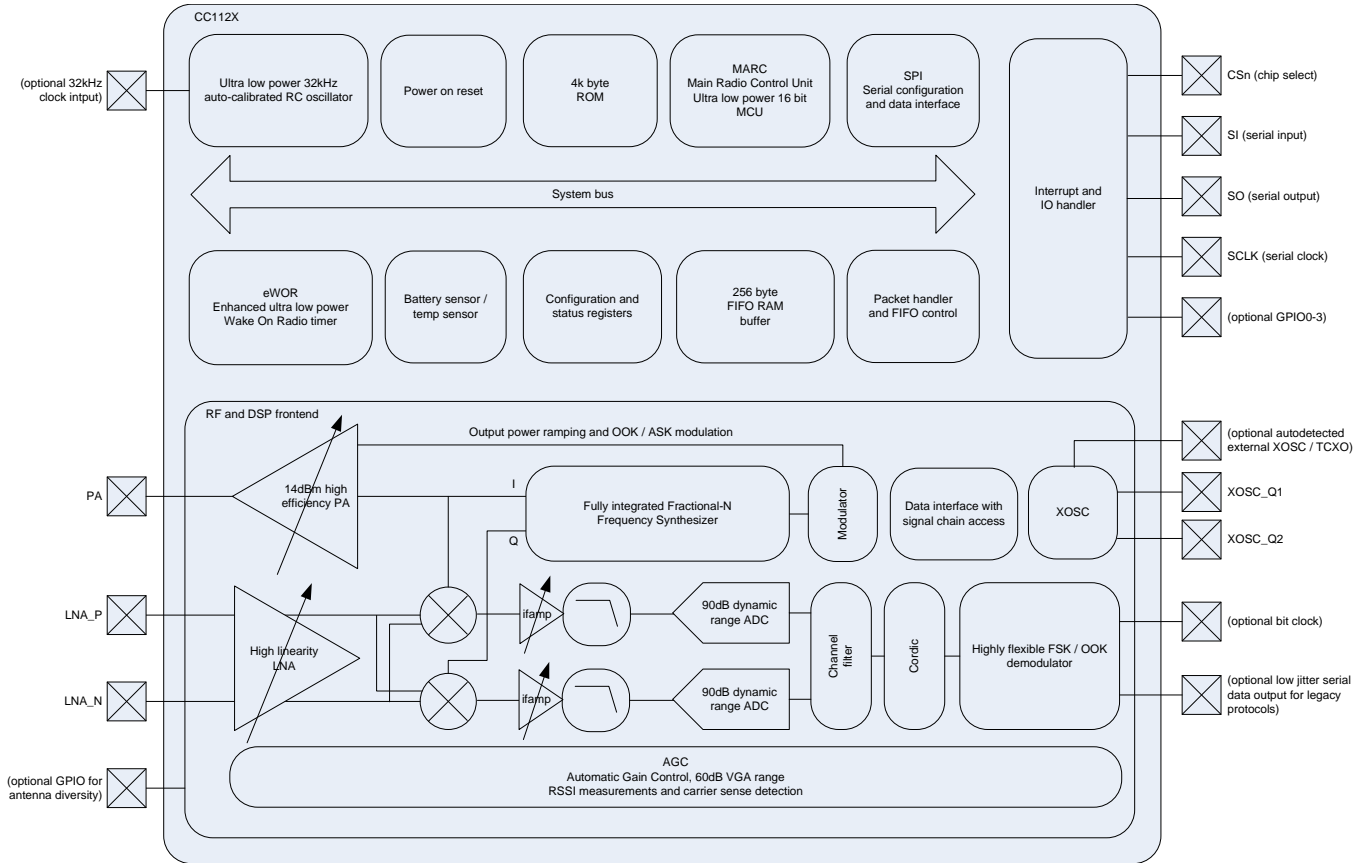


Figure 4-1. System Block Diagram

4.2 Frequency Synthesizer

At the center of the CC1120 device there is a fully integrated, fractional-N, ultra-high-performance frequency synthesizer. The frequency synthesizer is designed for excellent phase noise performance, providing very high selectivity and blocking performance. The system is designed to comply with the most stringent regulatory spectral masks at maximum transmit power.

Either a crystal can be connected to XOSC_Q1 and XOSC_Q2, or a TCXO can be connected to the EXT_XOSC input. The oscillator generates the reference frequency for the synthesizer, as well as clocks for the analog-to-digital (ADC) and the digital part. To reduce system cost, CC1120 device has high-accuracy frequency estimation and compensation registers to measure and compensate for crystal inaccuracies. This compensation enables the use of lower cost crystals. If a TCXO is used, the CC1120 device automatically turns on and off the TCXO when needed to support low-power modes and Wake-On-Radio operation.

4.3 Receiver

The CC1120 device features a highly flexible receiver. The received RF signal is amplified by the low-noise amplifier (LNA) and is down-converted in quadrature (I/Q) to the intermediate frequency (IF). At IF, the I/Q signals are digitized by the high dynamic-range ADCs.

An advanced automatic gain control (AGC) unit adjusts the front-end gain, and enables the CC1120 device to receive strong and weak signals, even in the presence of strong interferers. High-attenuation channels and data filtering enable reception with strong neighbor channel interferers. The I/Q signal is converted to a phase and magnitude signal to support the FSK and OOK modulation schemes.

NOTE

A novel I/Q compensation algorithm removes any problem of I/Q mismatch, thus avoiding time-consuming and costly I/Q image calibration steps.

4.4 Transmitter

The CC1120 transmitter is based on direct synthesis of the RF frequency (in-loop modulation). To use the spectrum effectively, the CC1120 device has extensive data filtering and shaping in TX mode to support high throughput data communication in narrowband channels. The modulator also controls power ramping to remove issues such as spectral splattering when driving external high-power RF amplifiers.

4.5 Radio Control and User Interface

The CC1120 digital control system is built around the main radio control (MARC), which is implemented using an internal high-performance, 16-bit ultra-low-power processor. MARC handles power modes, radio sequencing, and protocol timing.

A 4-wire SPI serial interface is used for configuration and data buffer access. The digital baseband includes support for channel configuration, packet handling, and data buffering. The host MCU can stay in power-down mode until a valid RF packet is received. This greatly reduces power consumption. When the host MCU receives a valid RF packet, it burst-reads the data. This reduces the required computing power.

The CC1120 radio control and user interface are based on the widely used CC1101 transceiver. This relationship enables an easy transition between the two platforms. The command strobes and the main radio states are the same for the two platforms.

For legacy formats, the CC1120 device also supports two serial modes.

- Synchronous serial mode: The CC1120 device performs bit synchronization and provides the MCU with a bit clock with associated data.
- Transparent mode: The CC1120 device outputs the digital baseband signal using a digital interpolation filter to eliminate jitter introduced by digital filtering and demodulation.

4.6 Enhanced Wake-On-Radio (eWOR)

eWOR, using a flexible integrated sleep timer, enables automatic receiver polling with no intervention from the MCU. When the CC1120 device enters RX mode, it listens and then returns to sleep if a valid RF packet is not received. The sleep interval and duty cycle can be configured to make a trade-off between network latency and power consumption. Incoming messages are time-stamped to simplify timer re-synchronization.

The eWOR timer runs off an ultra-low-power 32-kHz RC oscillator. To improve timing accuracy, the RC oscillator can be automatically calibrated to the RF crystal in configurable intervals.

4.7 Sniff Mode

The CC1120 device supports quick start up times, and requires few preamble bits. Sniff mode uses these conditions to dramatically reduce the current consumption while the receiver is waiting for data.

Because the CC1120 device can wake up and settle much faster than the duration of most preambles, it is not required to be in RX mode continuously while waiting for a packet to arrive. Instead, the enhanced Wake-On-Radio feature can be used to put the device into sleep mode periodically. By setting an appropriate sleep time, the CC1120 device can wake up and receive the packet when it arrives with no performance loss. This sequence removes the need for accurate timing synchronization between transmitter and receiver, and lets the user trade off current consumption between the transmitter and receiver.

For more information, see the sniff mode design note ([SWRA428](#)).

4.8 Antenna Diversity

Antenna diversity can increase performance in a multipath environment. An external antenna switch is required. The CC1201 device uses one of the GPIO pins to automatically control the switch. This device also supports differential output control signals typically used in RF switches.

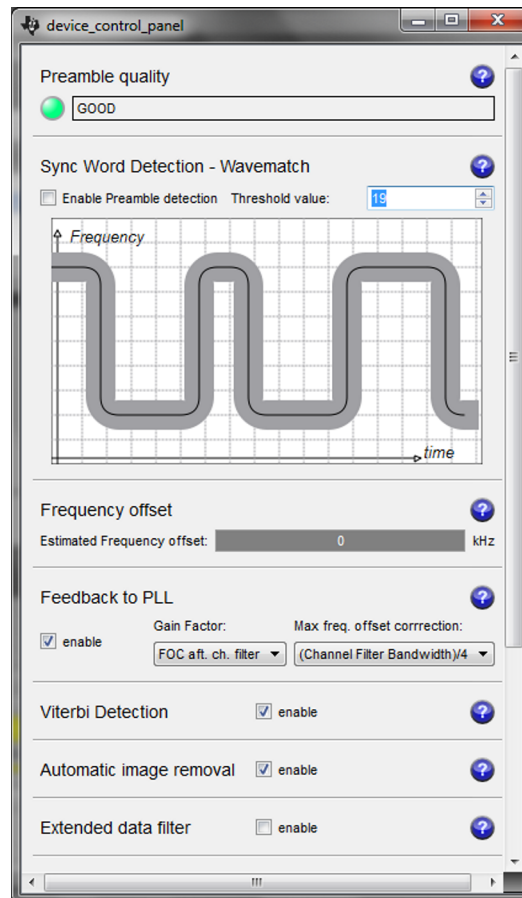
If antenna diversity is enabled, the GPIO alternates between high and low states until a valid RF input signal is detected. An optional acknowledge packet can be transmitted without changing the state of the GPIO.

An incoming RF signal can be validated by received signal strength or by using the automatic preamble detector. Using the automatic preamble detector ensures a more robust system and avoids the need to set a defined signal strength threshold (such a threshold sets the sensitivity limit of the system).

4.9 WaveMatch

Advanced capture logic locks onto the synchronization word and does not require preamble settling bytes. Therefore, receiver settling time is reduced to the settling time of the AGC, typically 4 bits.

The WaveMatch feature also greatly reduces false sync triggering on noise, further reducing the power consumption and improving sensitivity and reliability. The same logic can also be used as a high-performance preamble detector to reliably detect a valid preamble in the channel.



See [SWRC046](#) for more information.

Figure 4-2. Receiver Configurator in SmartRF Studio

5 Typical Application Circuit

NOTE

This section is intended only as an introduction.

Very few external components are required for the operation of the CC1120 device. Figure 5-1 shows a typical application circuit. The board layout will greatly influence the RF performance of the CC1120 device. Figure 5-1 does not show decoupling capacitors for power pins.

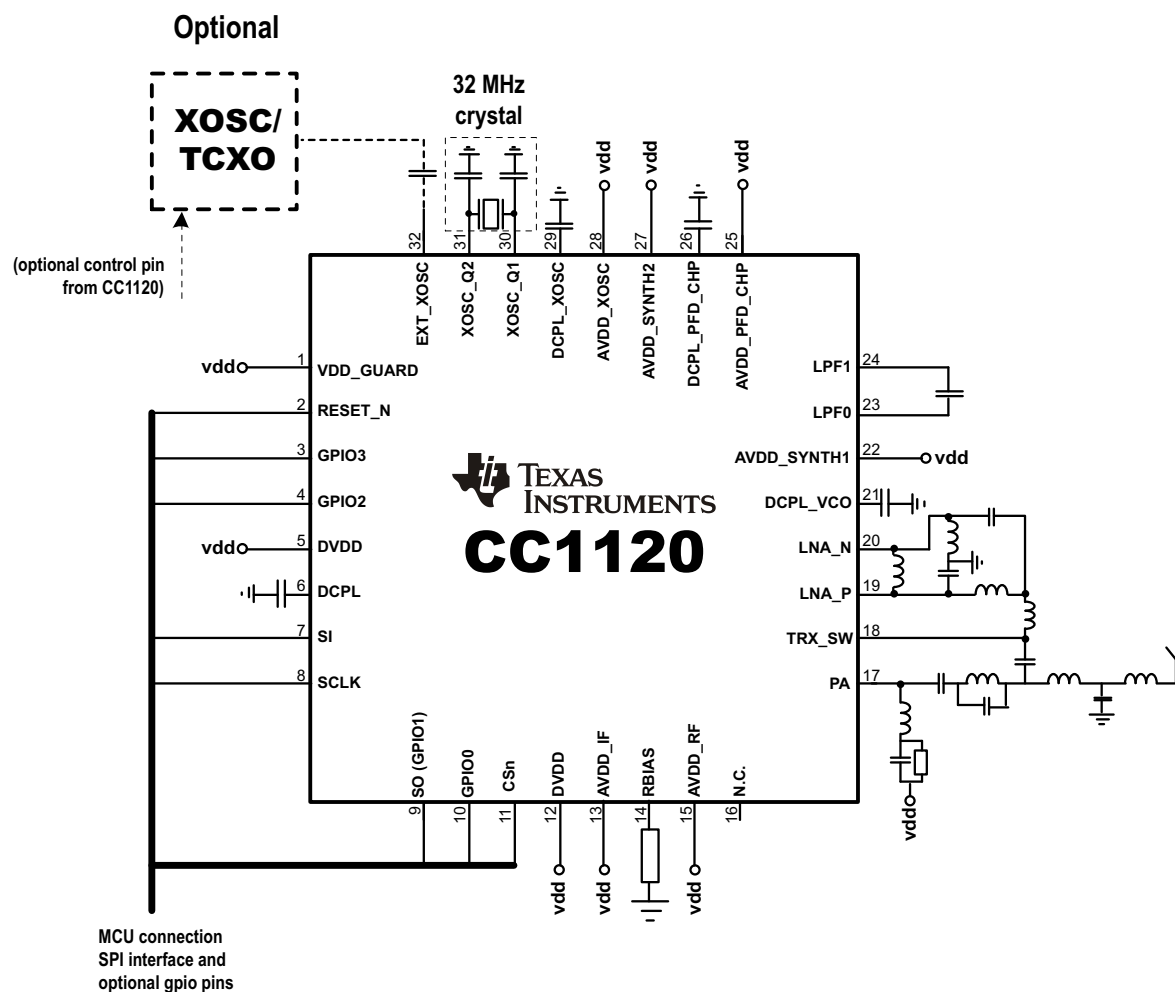


Figure 5-1. Typical Application Circuit

For more information, see the reference designs available for the CC1120 device:

- CC112x IPC 868- and 915-MHz 2-layer Reference Design ([SWRR106](#))
- CC112x IPC 868- and 915-MHz 4-layer Reference Design ([SWRR107](#))
- CC1120EM 169-MHz Reference Design ([SWRC220](#))
- CC1120EM 420- to 470-MHz Reference Design ([SWRC221](#))
- CC1120EM 868- to 915-MHz Reference Design ([SWRC222](#))
- CC1120EM 955-MHz Reference Design ([SWRC223](#)).

6 Configuration Software

The CC1120 device can be configured using the SmartRF™ Studio software ([SWRC046](#)). The SmartRF Studio software is highly recommended for obtaining optimum register settings, and for evaluating performance and functionality.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CC1120RHBR	ACTIVE	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1120	Samples
CC1120RHBT	ACTIVE	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1120	Samples
CC1120RHMR	NRND	VQFN	RHM	32	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	CC1120	
CC1120RHMT	NRND	VQFN	RHM	32	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	CC1120	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CC1120RHBR	VQFN	RHB	32	3000	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2
CC1120RHBT	VQFN	RHB	32	250	180.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2
CC1120RHMT	VQFN	RHM	32	250	180.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS

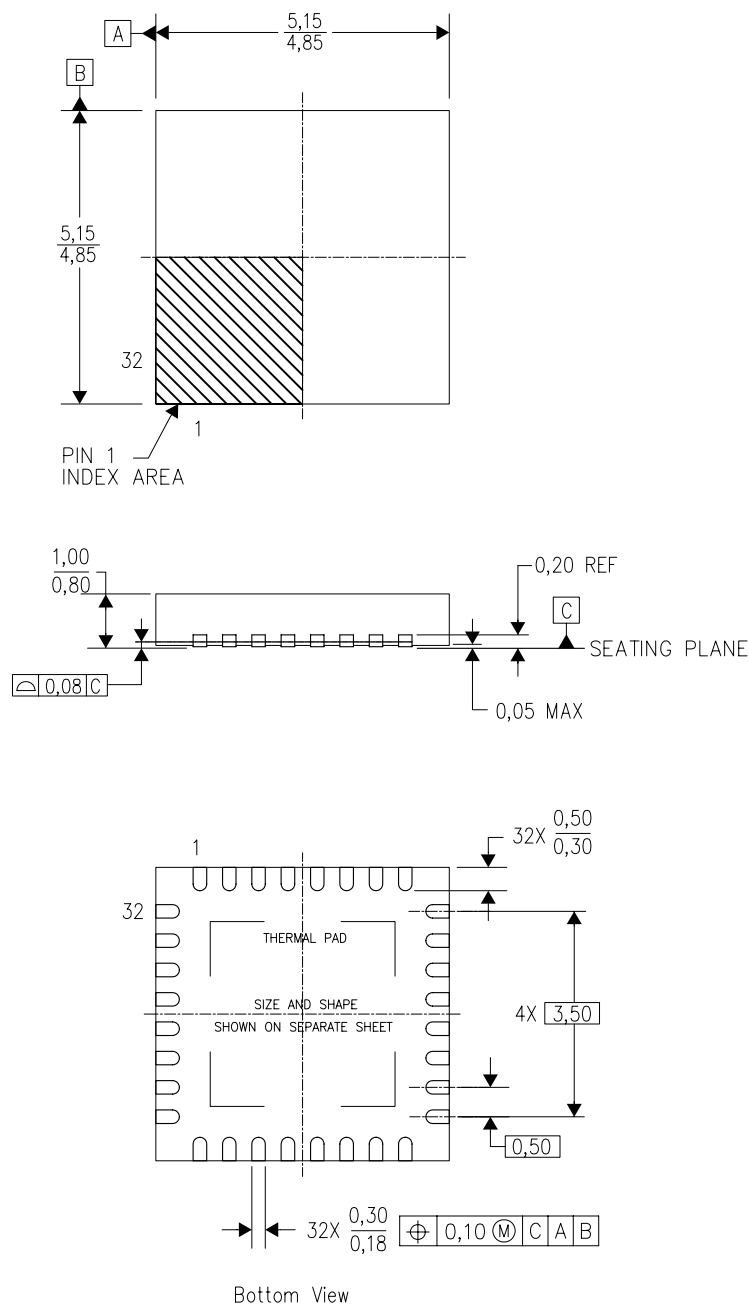


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CC1120RHBR	VQFN	RHB	32	3000	338.1	338.1	20.6
CC1120RHBT	VQFN	RHB	32	250	210.0	185.0	35.0
CC1120RHMT	VQFN	RHM	32	250	210.0	185.0	35.0

RHB (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



4204326/D 06/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. QFN (Quad Flatpack No-Lead) Package configuration.
 - D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
 - F. Falls within JEDEC MO-220.

RHB (S-PVQFN-N32)

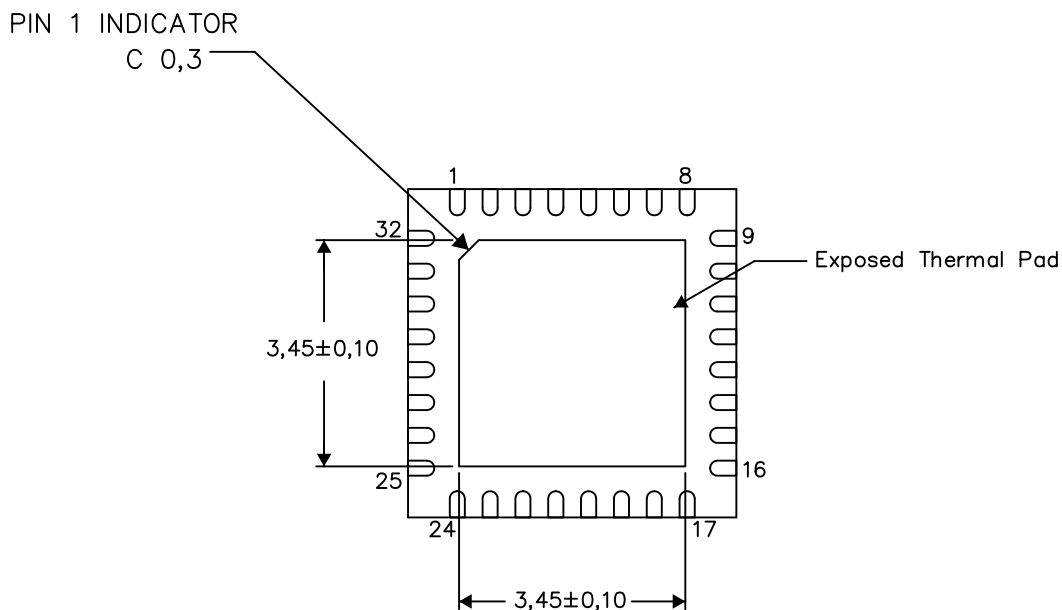
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

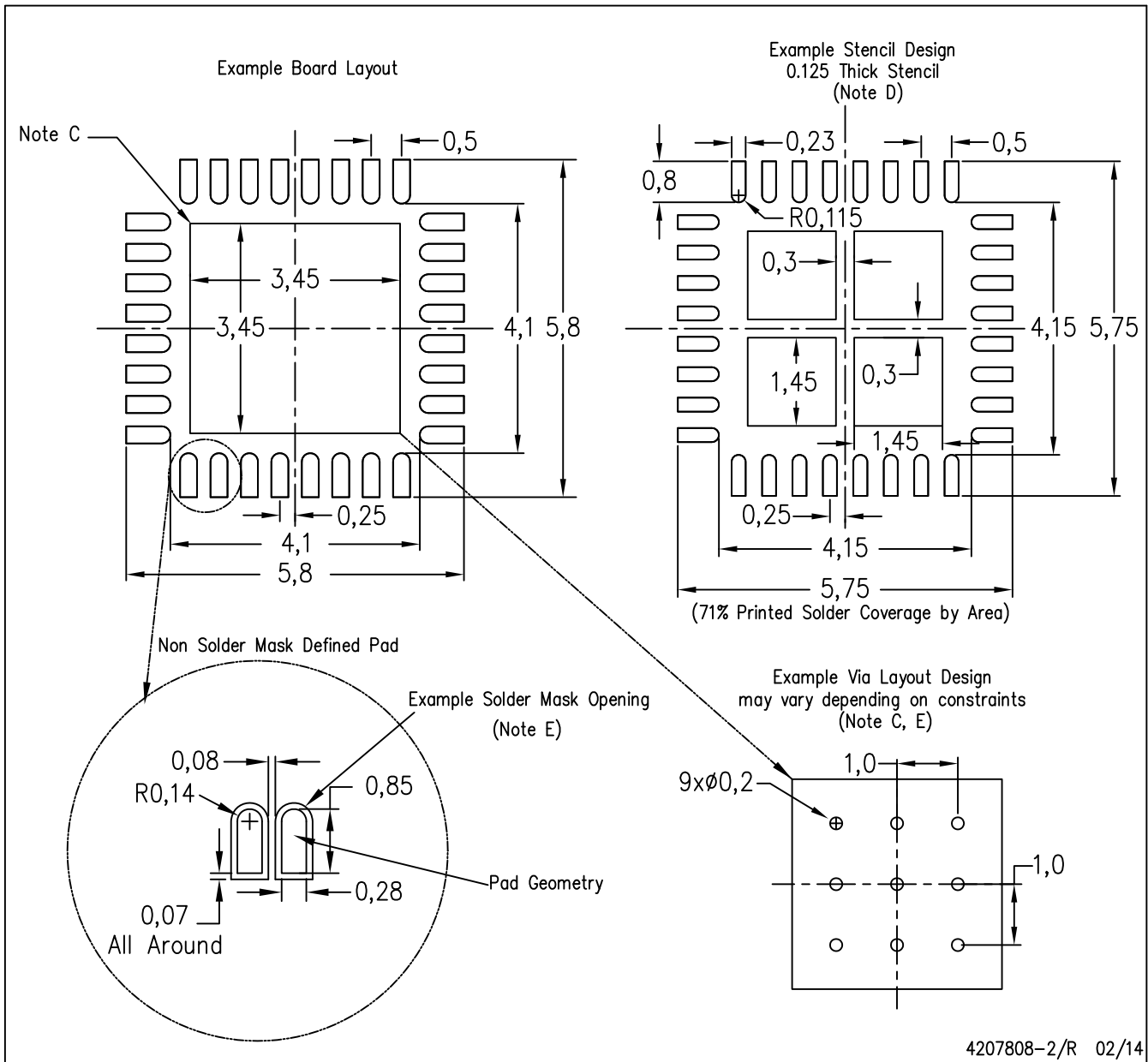
Exposed Thermal Pad Dimensions

4206356-2/Y 06/13

NOTE: A. All linear dimensions are in millimeters

RHB (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD

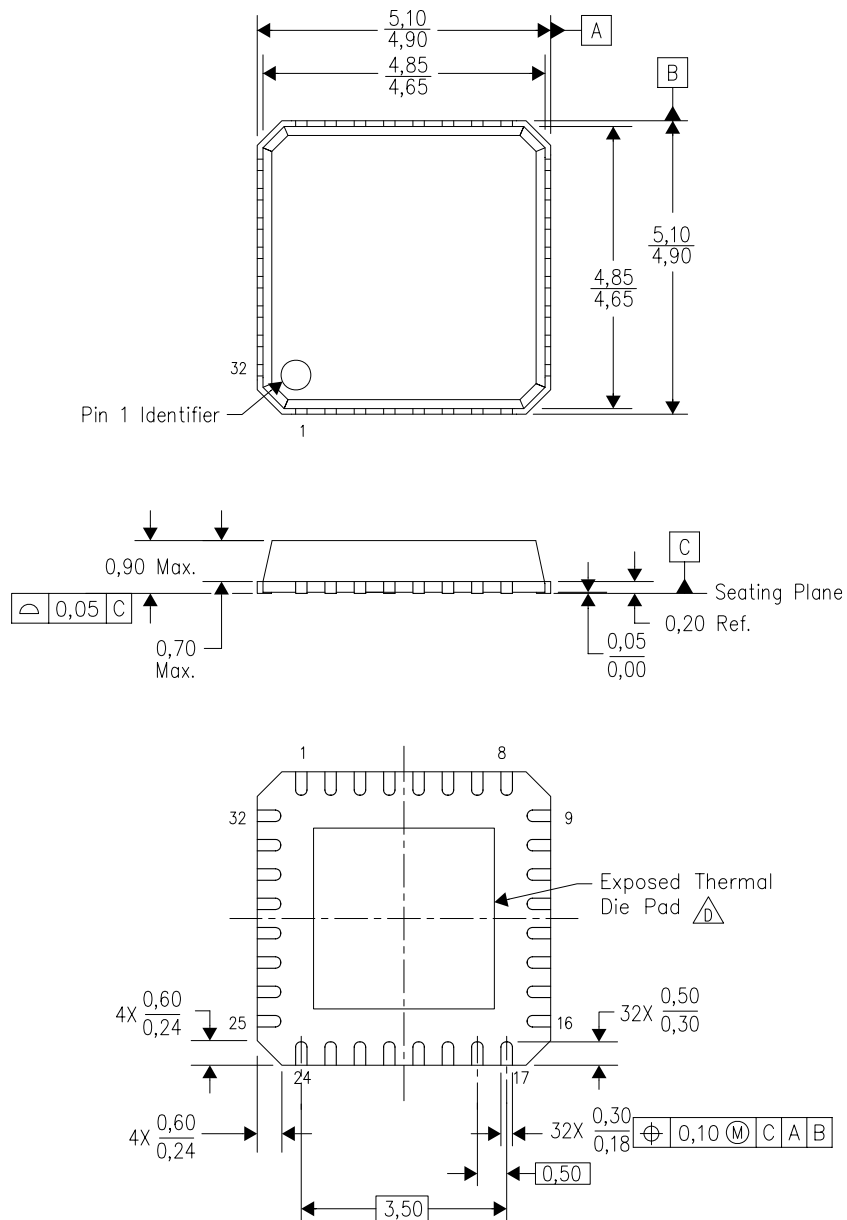


4207808-2/R 02/14


- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - E. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.

RHM (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



4205347/B 04/10

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. QFN (Quad Flatpack No-Lead) Package configuration.
-  The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.

THERMAL PAD MECHANICAL DATA

RHM (S-PVQFN-N32)

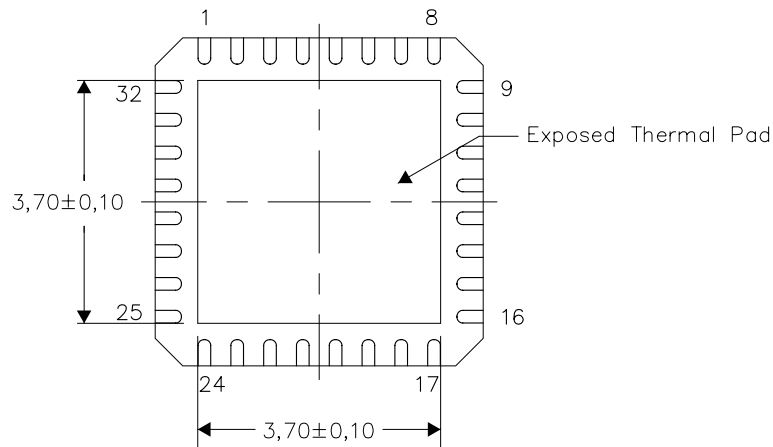
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



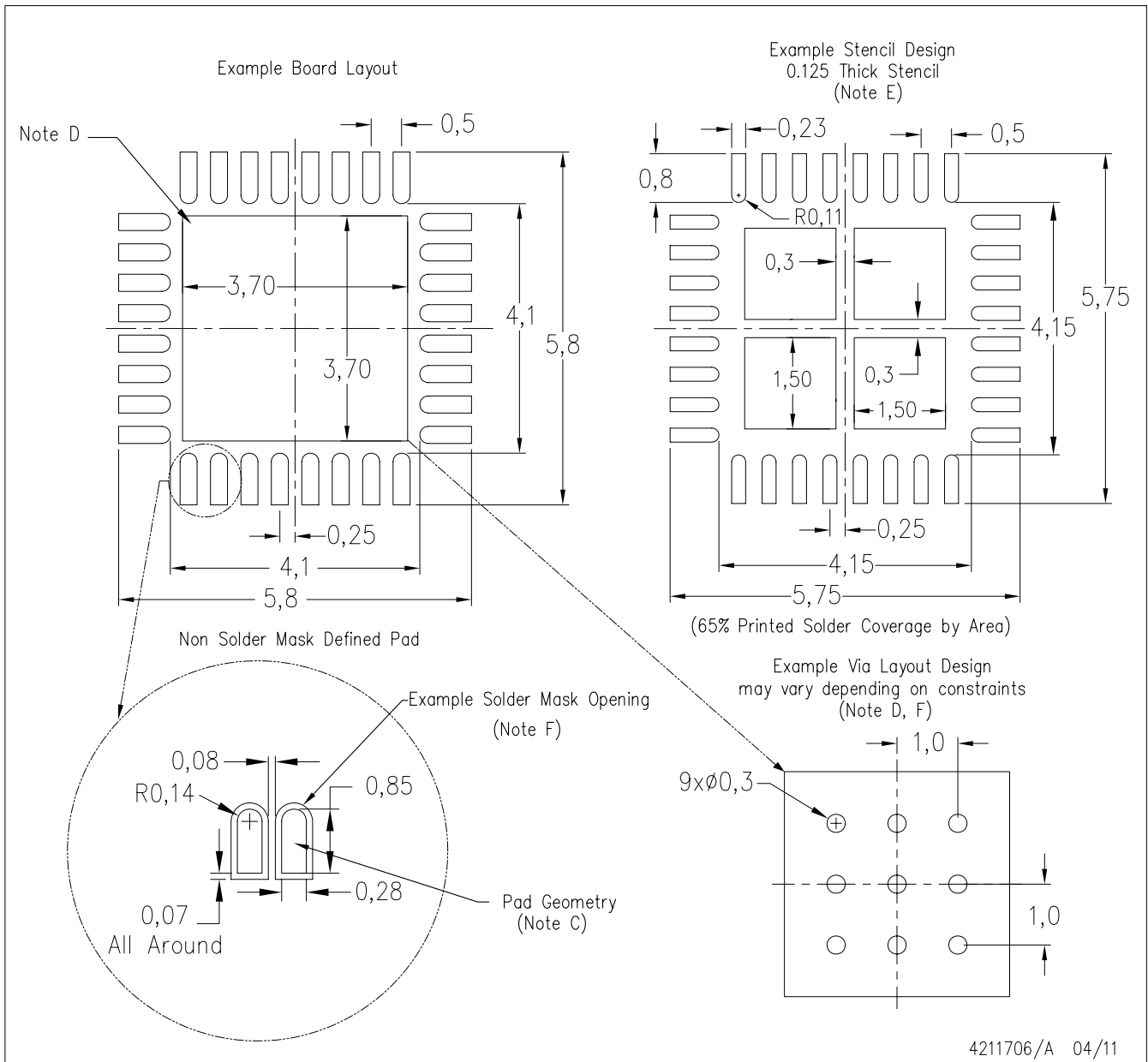
Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

RHM (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.

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